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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Chin-Yang Chen Examiner: WEISS, HOWARD.
Filing Date: 10/01/2001 Art Unit: 2814
Serial No.: 09/682,628 Docket No.: NAUP0384USA

Title: AN ANTI-FUSE STRUCTURE WITH LOW ON-STATE RESISTANCE AND LOW OFF-STATE LEAKAGE

To: Assistant Commissioner for Patents
Washington, D.C. 20231

Subject: Reply to Office action dated 07/03/2002

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Dear Sir:

AMENDMENT

In response to the Office action noted above, please amend the above-identified application as follows:

In the specification:

Please substitute the paragraph [0021] from page 5, with the following paragraph:

Please refer to Fig.3 to Fig.6 of schematic diagrams of several embodiments of an anti-fuse structure according the present invention. A semiconductor wafer 50 comprises a silicon substrate 52. An isolation layer 54 is positioned on the silicon substrate 52 and an anti-fuse structure 51 is set on the isolation layer 54. The anti-fuse structure

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